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(54) **THIN FILM TRANSISTOR DRIVING BACKPLANE AND MANUFACTURING METHOD THEREOF, AND DISPLAY PANEL**

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(57) **ABSTRACT**

The embodiments of the present invention provide a thin film transistor driving backplane and a manufacturing method thereof, and a display panel. The manufacturing method may comprise: manufacturing a backplane base disposed with a plurality of active device structures; disposing an electrode layer on the backplane base; and manufacturing the electrode layer into a source electrode, a drain electrode and a pixel electrode integrally disposed with the drain electrode by one patterning process. According to the embodiment of the present invention, the electrode layer is manufactured into a plurality of source electrodes, drain electrodes and pixel electrodes, integrally disposed with the drain electrode, by one time patterning process, so that the source electrode, the drain electrode and the pixel electrode are all at the same electrode layer, and the source electrode,

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